

BD240, BD240A, BD240B, BD240C

PNP SILICON POWER TRANSISTORS

BOURNS®

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$ (see Note 5)	$I_B = 0$	BD240 BD240A BD240B BD240C	-45 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -55 \text{ V}$ $V_{CE} = -70 \text{ V}$ $V_{CE} = -90 \text{ V}$ $V_{CE} = -115 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD240 BD240A BD240B BD240C			-0.2 -0.2 -0.2 -0.2	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	BD240/240A BD240B/240C			-0.3 -0.3	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-1	μA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -0.2 \text{ A}$ $I_C = -1 \text{ A}$	(see Notes 5 and 6)	40 15			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -0.2 \text{ A}$	$I_C = -1 \text{ A}$	(see Notes 5 and 6)			-0.7	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$	$I_C = -1 \text{ A}$	(see Notes 5 and 6)			-1.3	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.2 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.2 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			4.17	$^{\circ}\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^{\circ}\text{C/W}$

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -200 \text{ mA}$	$I_{B(on)} = -20 \text{ mA}$	$I_{B(off)} = 20 \text{ mA}$		0.2		μs
t_{off} Turn-off time	$V_{BE(off)} = 3.4 \text{ V}$	$R_L = 150 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$		0.4		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002

Specifications are subject to change without notice.

TYPICAL CHARACTERISTICS

**TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT**

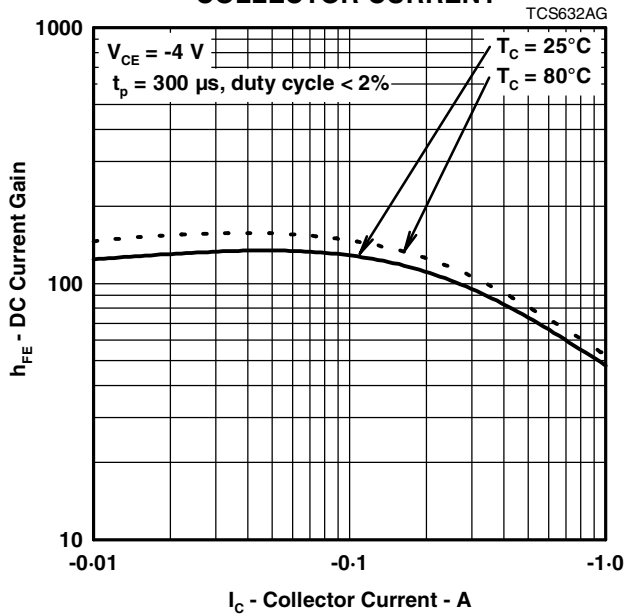


Figure 1.

**COLLECTOR-EMITTER SATURATION VOLTAGE
vs
BASE CURRENT**

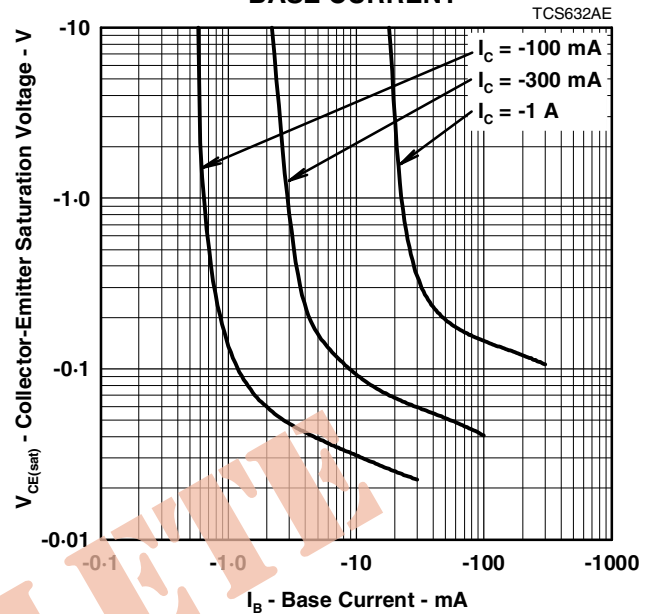


Figure 2.

**BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT**

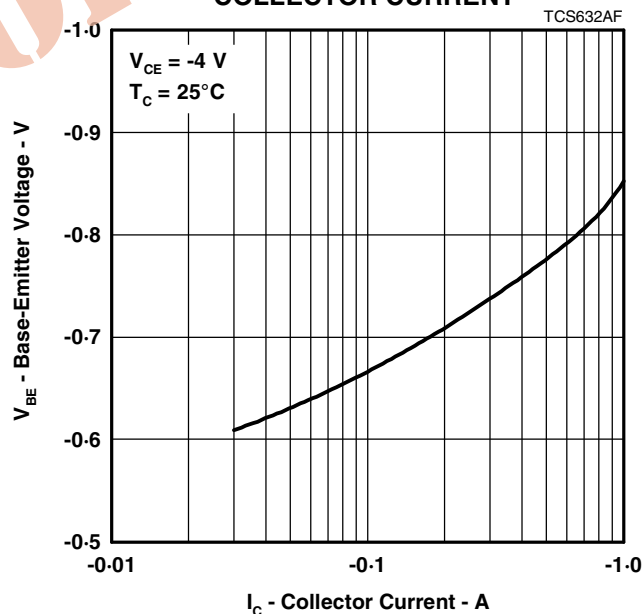


Figure 3.

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MAXIMUM SAFE OPERATING REGIONS

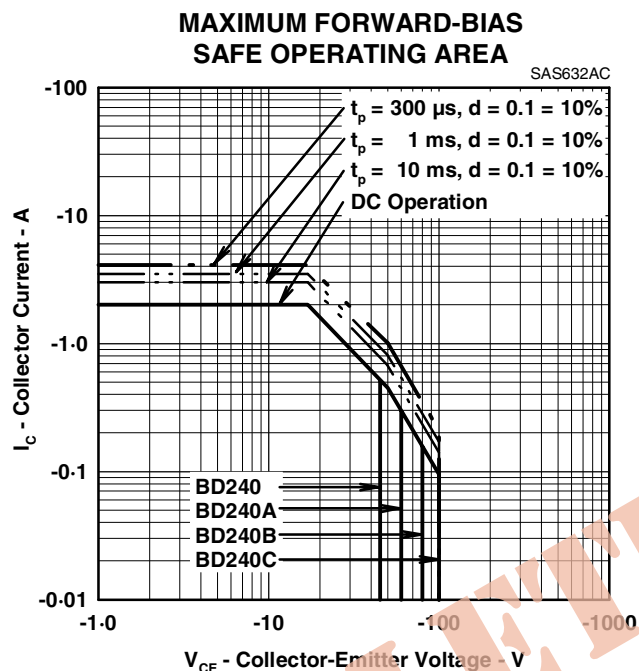


Figure 4.

THERMAL INFORMATION

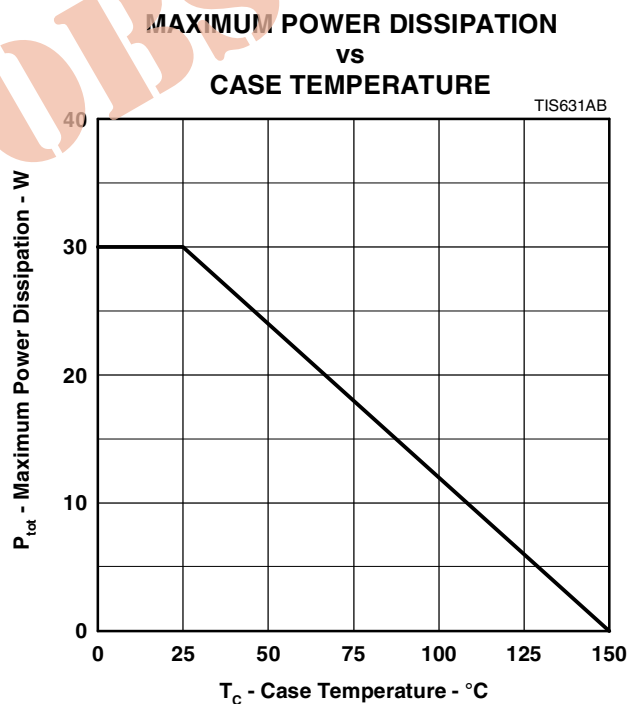


Figure 5.

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